



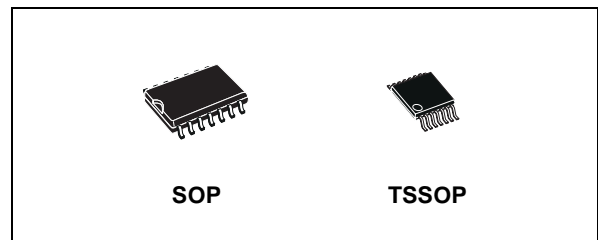
## 74LVQ00

### LOW VOLTAGE CMOS QUAD 2-INPUT NAND GATE

- **HIGH SPEED:**  
 $t_{PD} = 5.5\text{ns}$  (TYP.) at  $V_{CC} = 3.3\text{V}$
- **COMPATIBLE WITH TTL OUTPUTS**
- **LOW POWER DISSIPATION:**  
 $I_{CC} = 2\mu\text{A}$  (MAX.) at  $T_A = 25^\circ\text{C}$
- **LOW NOISE:**  
 $V_{OLP} = 0.3\text{V}$  (TYP.) at  $V_{CC} = 3.3\text{V}$
- **75Ω TRANSMISSION LINE DRIVING CAPABILITY**
- **SYMMETRICAL OUTPUT IMPEDANCE:**  
 $|I_{OH}| = I_{OL} = 12\text{mA}$  (MIN) at  $V_{CC} = 3.0\text{V}$
- **PCI BUS LEVELS GUARANTEED AT 24 mA**
- **BALANCED PROPAGATION DELAYS:**  
 $t_{PLH} \approx t_{PHL}$
- **OPERATING VOLTAGE RANGE:**  
 $V_{CC}(\text{OPR}) = 2\text{V to } 3.6\text{V}$  (1.2V Data Retention)
- **PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 00**
- **IMPROVED LATCH-UP IMMUNITY**

#### DESCRIPTION

The 74LVQ00 is a low voltage CMOS QUAD 2-INPUT NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS



#### ORDER CODES

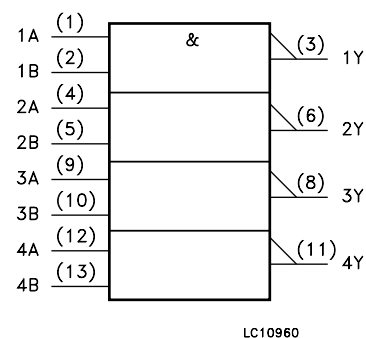
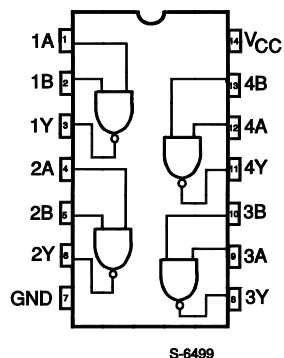
PACKAGE	TUBE	T & R
SOP	74LVQ00M	74LVQ00MTR
TSSOP		74LVQ00TTR

technology. It is ideal for low power and low noise 3.3V applications.

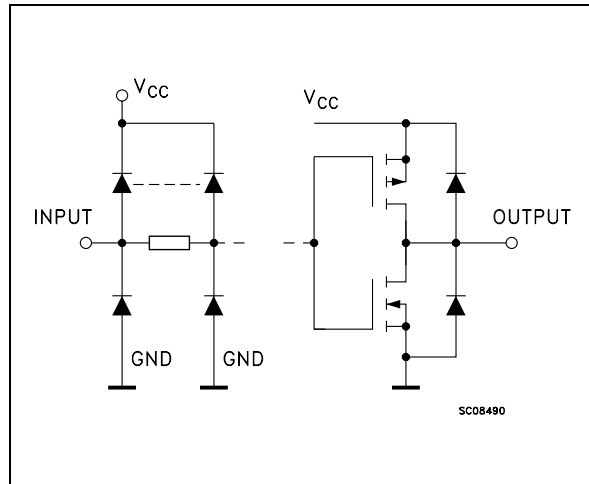
The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

#### PIN CONNECTION AND IEC LOGIC SYMBOLS



## INPUT AND OUTPUT EQUIVALENT CIRCUIT



## PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V <sub>CC</sub>	Positive Supply Voltage

## TRUTH TABLE

A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	± 50	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 200	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage (note 1)	2 to 3.6	V
V <sub>I</sub>	Input Voltage	0 to V <sub>CC</sub>	V
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time V <sub>CC</sub> = 3.0V (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.2V to 3.6V

2) V<sub>IN</sub> from 0.8V to 2V

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>IH</sub>	High Level Input Voltage	3.0 to 3.6		2.0			2.0		2.0		V
V <sub>IL</sub>	Low Level Input Voltage					0.8		0.8		0.8	V
V <sub>OH</sub>	High Level Output Voltage	3.0	I <sub>O</sub> =-50 μA	2.9	2.99		2.9		2.9		V
			I <sub>O</sub> =-12 mA	2.58			2.48		2.48		
			I <sub>O</sub> =-24 mA				2.2		2.2		
V <sub>OL</sub>	Low Level Output Voltage	3.0	I <sub>O</sub> =50 μA		0.002	0.1		0.1		0.1	V
			I <sub>O</sub> =12 mA		0	0.36		0.44		0.44	
			I <sub>O</sub> =24 mA					0.55		0.55	
I <sub>I</sub>	Input Leakage Current	3.6	V <sub>I</sub> = V <sub>CC</sub> or GND			± 0.1		± 1		± 1	μA
I <sub>CC</sub>	Quiescent Supply Current	3.6	V <sub>I</sub> = V <sub>CC</sub> or GND			2		20		20	μA
I <sub>OLD</sub>	Dynamic Output Current (note 1, 2)	3.6	V <sub>OLD</sub> = 0.8 V max				36		25		mA
I <sub>OHD</sub>			V <sub>OHD</sub> = 2 V min				-25		-25		mA

1) Maximum test duration 2ms, one output loaded at time

2) Incident wave switching is guaranteed on transmission lines with impedances as low as 75Ω

## DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>OLP</sub>	Dynamic Low Voltage Quiet Output (note 1, 2)	3.3	C <sub>L</sub> = 50 pF		0.3	0.8					V
V <sub>OLV</sub>				-0.8	-0.3						
V <sub>IHD</sub>	Dynamic High Voltage Input (note 1, 3)	3.3		2							V
V <sub>ILD</sub>	Dynamic Low Voltage Input (note 1, 3)	3.3					0.8				

1) Worst case package.

2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.3V, (n-1) outputs switching and one output at GND.

3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.3V. Inputs under test switching: 3.3V to threshold (V<sub>ILD</sub>), 0V to threshold (V<sub>IHD</sub>), f=1MHz.

**AC ELECTRICAL CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ ,  $R_L = 500 \Omega$ , Input  $t_r = t_f = 3 \text{ ns}$ )

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time	2.7		.	6.0	11.0		12.0		14.0	ns
		3.3(*)			5.5	8.0		9.0		10.0	
t <sub>OSLH</sub> t <sub>OSHL</sub>	Output To Output Skew Time (note1, 2)	2.7			0.5	1.0		1.0		1.0	ns
		3.3(*)			0.5	1.0		1.0		1.0	

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ( $t_{OSLH} = |t_{PLHm} - t_{PLHn}|$ ,  $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$ )

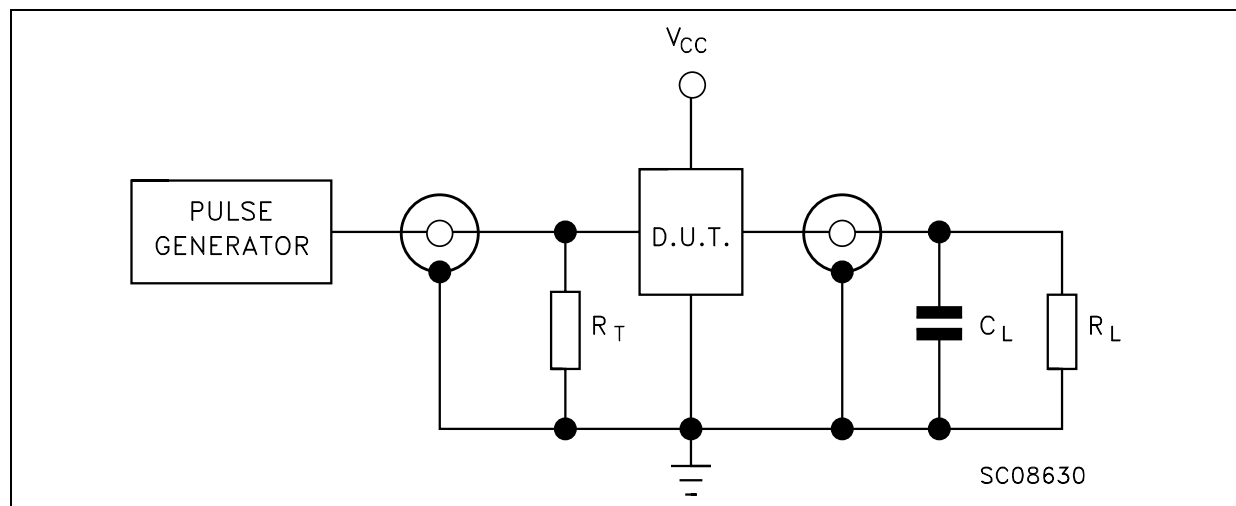
2) Parameter guaranteed by design

(\*) Voltage range is  $3.3\text{V} \pm 0.3\text{V}$

**CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C <sub>IN</sub>	Input Capacitance	3.3			4						pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	3.3	f <sub>IN</sub> = 10MHz		24						pF

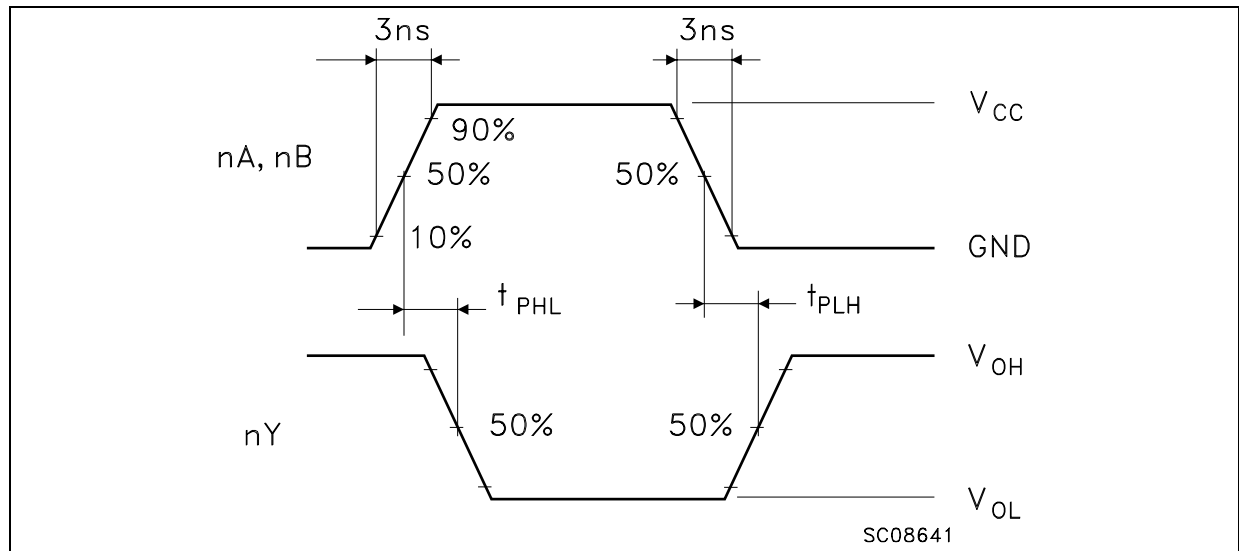
1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$  (per gate)

**TEST CIRCUIT**

$C_L = 50\text{pF}$  or equivalent (includes jig and probe capacitance)

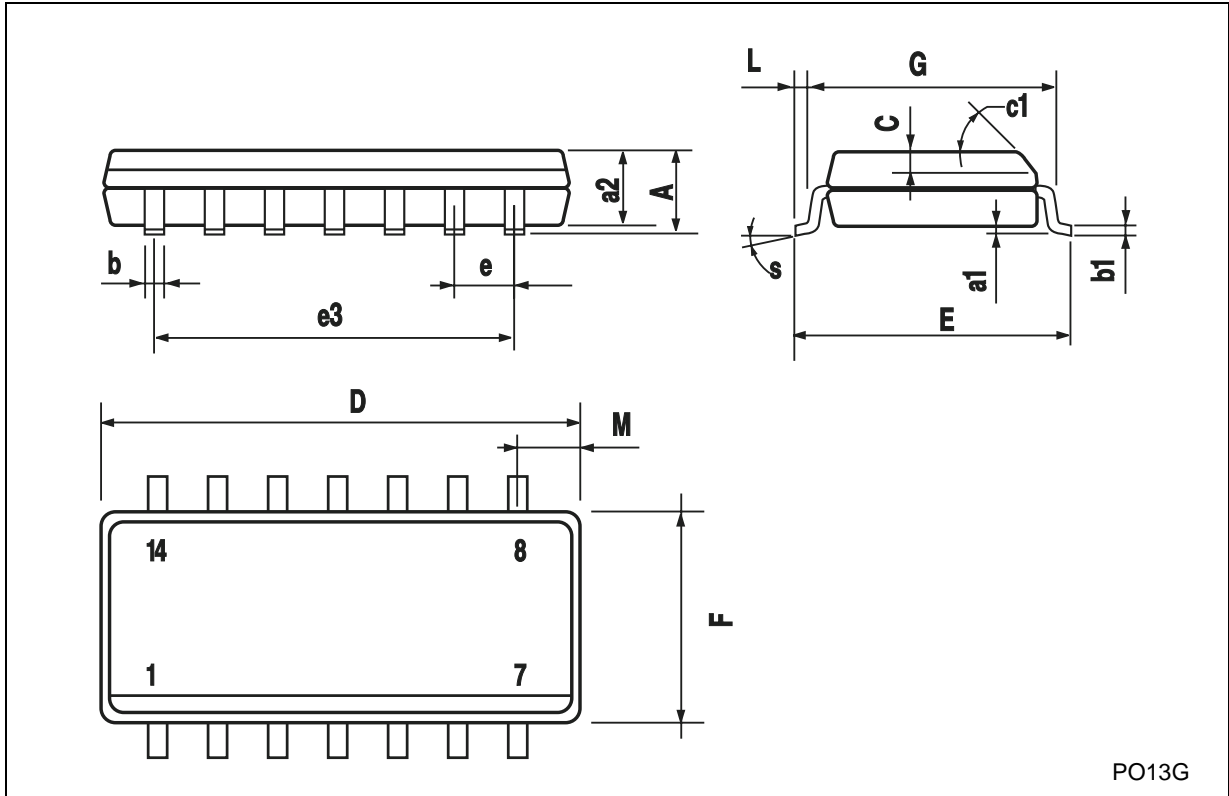
$R_L = 500\Omega$  or equivalent

$R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

**WAVEFORM: PROPAGATION DELAYS** ( $f=1\text{MHz}$ ; 50% duty cycle)

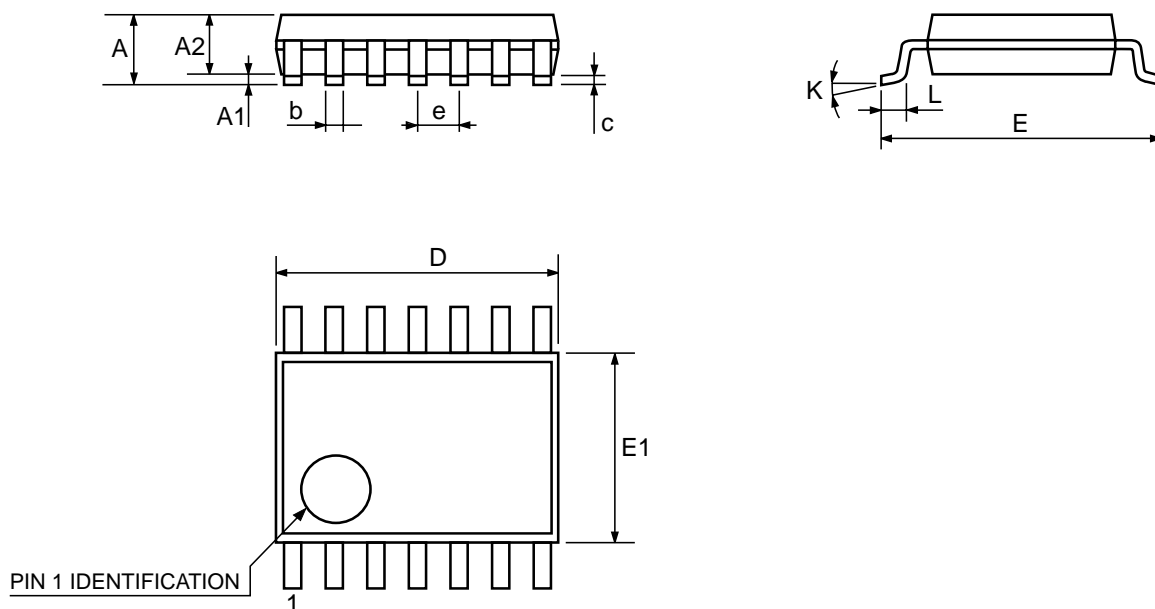
SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



## TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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